

Zbig R Wasilewski

List of Publications by Year in descending order

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258
papers

9,541
citations

38660

50
h-index

45213

90
g-index

259
all docs

259
docs citations

259
times ranked

5512
citing authors

#	ARTICLE	IF	CITATIONS
1	A Tunable Unidirectional Source for GUSTO™s Local Oscillator at 4.74 THz. IEEE Transactions on Terahertz Science and Technology, 2022, 12, 144-150.	2.0	8
2	Effects of biased and unbiased illuminations on two-dimensional electron gases in dopant-free GaAs/AlGaAs. Physical Review B, 2022, 105, .	1.1	2
3	High-power portable terahertz laser systems. Nature Photonics, 2021, 15, 16-20.	15.6	228
4	High current density tunnel diodes for multi-junction photovoltaic devices on InP substrates. Applied Physics Letters, 2021, 118, .	1.5	13
5	Precise control of time-varying effusion cell flux in molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 043407.	0.9	3
6	Non-adiabatic single-electron pumps in a dopant-free GaAs/AlGaAs 2DEG. Applied Physics Letters, 2021, 119, .	1.5	5
7	Realization of Harmonic Oscillator Arrays with Graded Semiconductor Quantum Wells. Physical Review Letters, 2020, 125, 097403.	2.9	15
8	MBE growth of continuously-graded parabolic quantum well arrays in AlGaAs. Journal of Crystal Growth, 2019, 514, 103-108.	0.7	19
9	Hillock-free and atomically smooth InSb QWs grown on GaAs substrates by MBE. Journal of Crystal Growth, 2019, 513, 15-19.	0.7	5
10	Room temperature THz intersubband transitions in continuously-graded Al _x Ga _{1-x} As parabolic quantum wells. , 2019, , .		0
11	Thin film metrology and microwave loss characterization of indium and aluminum/indium superconducting planar resonators. Journal of Applied Physics, 2018, 123, .	1.1	7
12	Threading dislocations in MBE grown AlInSb metamorphic buffers: Revealed and counted. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	3
13	Optimization of metamorphic buffers for MBE growth of high quality AlInSb/InSb quantum structures: Suppression of hillock formation. Journal of Crystal Growth, 2017, 477, 7-11.	0.7	8
14	Temperature monitoring of narrow bandgap semiconductors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	5
15	Microscopic model for the magnetic-field-driven breakdown of the dissipationless state in the integer and fractional quantum Hall effect. Physical Review B, 2016, 94, .	1.1	2
16	Growth and characterization of epitaxial aluminum layers on gallium-arsenide substrates for superconducting quantum bits. Superconductor Science and Technology, 2016, 29, 064004.	1.8	7
17	Role of metastable charge states in a quantum-dot spin-qubit readout. Physical Review B, 2015, 92, .	1.1	12
18	Effects of interface roughness scattering on device performance of indirectly pumped terahertz quantum cascade lasers. Journal of Physics: Conference Series, 2015, 619, 012003.	0.3	10

#	ARTICLE	IF	CITATIONS
19	Scanning Voltage Microscopy Study of Lasing and Non-lasing Terahertz Quantum Cascade Lasers. , 2015, , .		0
20	Excitonic complexes in natural InAs/GaAs quantum dots. Physical Review B, 2015, 91, .	1.1	30
21	Three-spin coherent oscillations and interference. Physical Review B, 2015, 91, .	1.1	7
22	Visibility study of S oscillations without applied initialization. Physical Review B, 2015, 91, .		
23	W line shape in the resistively detected nuclear magnetic resonance. Journal of Physics Condensed Matter, 2015, 27, 275801.	0.7	5
24	AlGaIn cladding-free 482 nm continuous wave nitride laser diodes grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, 02C112.	0.6	0
25	A high carrier injection terahertz quantum cascade laser based on indirectly pumped scheme. Applied Physics Letters, 2014, 104, 041111.	1.5	19
26	Experimental investigation of terahertz quantum cascade laser with variable barrier heights. Journal of Applied Physics, 2014, 115, 163103.	1.1	14
27	True-blue laser diodes grown by plasma-assisted MBE on bulk GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 666-669.	0.8	3
28	Nitride-based laser diodes grown by plasma-assisted molecular beam epitaxy. Journal Physics D: Applied Physics, 2014, 47, 073001.	1.3	56
29	An indirectly pumped terahertz quantum cascade laser with low injection coupling strength operating above 150 K. Journal of Applied Physics, 2013, 113, .	1.1	28
30	Role of nonequivalent atomic step edges in the growth of InGaIn by plasma-assisted molecular beam epitaxy. Proceedings of SPIE, 2013, , .	0.8	2
31	True-blue nitride laser diodes grown by plasma assisted MBE on low dislocation density GaN substrates. Proceedings of SPIE, 2013, , .	0.8	0
32	Dispersive line shape in the vicinity of the $\frac{1}{2}$ Hall state: Coexistence of Knight-shifted and unshifted resistively detected NMR responses. Physical Review B, 2013, 88, .	1.1	12
33	Effect of oscillator strength and intermediate resonance on the performance of resonant phonon-based terahertz quantum cascade lasers. Journal of Applied Physics, 2013, 113, 113109.	1.1	38
34	Nonequivalent atomic step edges – Role of gallium and nitrogen atoms in the growth of InGaIn layers. Journal of Crystal Growth, 2013, 367, 115-121.	0.7	46
35	Bipolar spin blockade and coherent state superpositions in a triple quantum dot. Nature Nanotechnology, 2013, 8, 261-265.	15.6	83
36	Enhanced charge detection: Amplification factor, phase reversal and measurement time dependence. , 2013, , .		0

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37	Classical percolation fingerprints in the high temperature regime of the quantum Hall effect. New Journal of Physics, 2013, 15, 083027.	1.2	6
38	THz quantum cascade lasers for operation above cryogenic temperatures. , 2013, , .		1
39	Role of Nonequivalent Atomic Step Edges in the Growth of InGaN by Plasma-Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE02.	0.8	4
40	Coherent manipulation of three-spin states in a GaAs/AlGaAs triple dot device. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 752-755.	0.8	1
41	Renormalization of effective mass in self-assembled quantum dots due to electron-electron interactions. Journal of Physics: Conference Series, 2013, 456, 012002.	0.3	0
42	Rate Equation Analysis of Three Phonon-Photon-Phonon Terahertz Quantum Cascade Lasers. , 2013, , .		0
43	Terahertz Quantum Cascade Laser Performance for Structures with Variable Barrier Heights. , 2013, , .		0
44	From laterally modulated two-dimensional electron gas towards artificial graphene. New Journal of Physics, 2012, 14, 053002.	1.2	59
45	InGaN laser diodes operating at 450-460 nm grown by rf-plasma MBE. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 02B102.	0.6	17
46	Terahertz quantum cascade lasers operating up to ≈ 200 K with optimized oscillator strength and improved injection tunneling. Optics Express, 2012, 20, 3866.	1.7	493
47	Photovoltaic infrared detection with p-type graded barrier heterostructures. Journal of Applied Physics, 2012, 111, .	1.1	11
48	Nonlinear magnetotransport phenomena in high-mobility two-dimensional electrons in InGaAs/InP and GaAs/AlGaAs. Physical Review B, 2012, 86, .	1.1	8
49	Induced currents in the quantum Hall regime: Energy storage, persistence, and $\langle I \rangle = \frac{1}{2} \frac{dQ}{dt}$ characteristics. Physical Review B, 2012, 86, .	1.1	0
50	Quantum Interference between Three Two-Spin States in a Double Quantum Dot. Physical Review Letters, 2012, 108, 226802.	2.9	24
51	Coherent exchange and double beam splitter oscillations in a triple quantum dot. Physical Review B, 2012, 86, .	1.1	14
52	The effect of In-flush on the optical anisotropy of InAs/GaAs quantum dots. Journal of Applied Physics, 2012, 111, 033510.	1.1	6
53	Terahertz Quantum Cascade Lasers Based on Phonon Scattering Assisted Injection and Extraction. , 2012, , .		1
54	199.5 K Operation of THz Quantum Cascade Lasers. , 2012, , .		0

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55	Enhanced charge detection of spin qubit readout via an intermediate state. Applied Physics Letters, 2012, 101, .	1.5	40
56	Coherent control of three-spin states in a triple quantum dot. Nature Physics, 2012, 8, 54-58.	6.5	215
57	A phonon scattering assisted injection and extraction based terahertz quantum cascade laser. Journal of Applied Physics, 2012, 111, .	1.1	58
58	Quantum interference and phonon-mediated back-action in lateral quantum-dot circuits. Nature Physics, 2012, 8, 522-527.	6.5	50
59	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 03C136.	0.6	25
60	Photo detectors for multi-spectral sensing. , 2011, , .		2
61	Metal-Grating-Coupled Terahertz Quantum-Well Photodetectors. IEEE Electron Device Letters, 2011, 32, 659-661.	2.2	31
62	Design of Laser Transition Oscillator Strength for THz Quantum Cascade Lasers. , 2011, , .		0
63	Phonon and polaron enhanced IR-THz photodetectors. , 2011, , .		1
64	Room temperature photovoltaic response of split-off band infrared detectors with a graded barrier. , 2011, , .		0
65	Single-photon emission from the natural quantum dots in the InAs/GaAs wetting layer. Physical Review B, 2011, 84, .	1.1	7
66	Intersubband impact ionization in THz QWIPs: shaping band structure reorganizations to design novel detectors. Proceedings of SPIE, 2011, , .	0.8	0
67	Terahertz detection by field effect transistors security imaging. Proceedings of SPIE, 2011, , .	0.8	0
68	Quantum Hall induced currents and the magnetoresistance of a quantum point contact. New Journal of Physics, 2011, 13, 123020.	1.2	2
69	Analysis of Dark Current Mechanisms for Split-Off Band Infrared Detectors at High Temperatures. IEEE Transactions on Electron Devices, 2010, 57, 1230-1236.	1.6	8
70	Time-Resolved Thermal Quenching of THz Quantum Cascade Lasers. IEEE Journal of Quantum Electronics, 2010, 46, 396-404.	1.0	19
71	Polarization Sensitivity of Quantum Well Infrared Photodetector Coupled to a Metallic Diffraction Grid. IEEE Journal of Quantum Electronics, 2010, 46, 877-883.	1.0	10
72	High contrast ratio, high uniformity multiple quantum well spatial light modulators. Journal of Semiconductors, 2010, 31, 034007.	2.0	1

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73	Five-band bias-selectable integrated quantum well detector in an n-p-n architecture. Applied Physics Letters, 2010, 97, .	1.5	5
74	Light-hole and heavy-hole transitions for high-temperature long-wavelength infrared detection. Applied Physics Letters, 2010, 97, .	1.5	43
75	Three-dimensional transport diagram of a triple quantum dot. Physical Review B, 2010, 82, .	1.1	74
76	Publisher's Note: Quantum oscillations in the microwave magnetoabsorption of a two-dimensional electron gas [Phys. Rev. B 81 (2010)]. Physical Review B, 2010, 81, .	1.1	3
77	Quantum oscillations in the microwave magnetoabsorption of a two-dimensional electron gas. Physical Review B, 2010, 81, .	1.1	43
78	Waveguide design for bi-modal operation of THz quantum cascade lasers. , 2010, , .		0
79	Electrically switching transverse modes in high power THz quantum cascade lasers. Optics Express, 2010, 18, 10036.	1.7	12
80	Electrically Controlling Beam Pattern of THz Quantum Cascade Lasers. , 2010, , .		0
81	Impact ionization in THz QWIPs. , 2009, , .		0
82	Multi-color infrared sensing with superlattice quantum dot structures and absorption enhancements. , 2009, , .		0
83	The effect of phonon extraction level separation on the performance of three-well resonant-phonon terahertz quantum-cascade lasers. Semiconductor Science and Technology, 2009, 24, 065012.	1.0	4
84	Temperature dependence of current-voltage characteristics of terahertz quantum-well photodetectors. Semiconductor Science and Technology, 2009, 24, 115014.	1.0	6
85	Three-dimensional localization of excitons in the InAs/GaAs wetting layer - magnetospectroscopic study. Physica Status Solidi (B): Basic Research, 2009, 246, 850-853.	0.7	3
86	InGaN light emitting diodes for 415 nm-520 nm spectral range by plasma assisted MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S917.	0.8	32
87	Nitride-based laser diodes by plasma-assisted MBE - From violet to green emission. Journal of Crystal Growth, 2009, 311, 1632-1639.	0.7	45
88	Terahertz quantum well infrared detectors. Infrared Physics and Technology, 2009, 52, 289-293.	1.3	15
89	Normal incidence detection of ultraviolet, visible, and mid-infrared radiation in a single GaAs/AlGaAs device. Optics Letters, 2009, 34, 2036.	1.7	10
90	Mode-locked pulses from mid-infrared Quantum Cascade Lasers. Optics Express, 2009, 17, 12929.	1.7	168

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91	Optimal Doping Density for Quantum-Well Infrared Photodetector Performance. IEEE Journal of Quantum Electronics, 2009, 45, 623-628.	1.0	18
92	Designing phonons for active use in terahertz devices. , 2009, , .		0
93	Terahertz Quantum Well Photodetectors. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 374-377.	1.9	33
94	Uncooled infrared detectors for 3-5 μ m and beyond. Applied Physics Letters, 2008, 93, .	1.5	47
95	Quantum dots for terahertz generation. Journal of Physics Condensed Matter, 2008, 20, 384211.	0.7	3
96	Natural quantum dots in the InAs/GaAs wetting layer. Applied Physics Letters, 2008, 92, 171104.	1.5	27
97	Photon upconversion devices for imaging. , 2008, , .		0
98	Decay of long-lived quantum Hall induced currents in 2D electron systems. New Journal of Physics, 2007, 9, 71-71.	1.2	8
99	Terahertz Quantum Cascade Lasers. , 2007, , .		1
100	Mid-infrared optical upconversion by integrating an InAsSb photodetector with a GaAs light emitting diode. , 2007, , .		0
101	Influence of the single-particle Zeeman energy on the quantum Hall ferromagnet at high filling factors. Physical Review B, 2007, 75, .	1.1	11
102	Quantum-Cascade Lasers with One-Well Injector Operating at 1.59 THz (= 188.5 μ m). , 2007, , .		3
103	Fano resonance mediated by intersubband-phonon coupling. Applied Physics Letters, 2007, 91, 131121.	1.5	12
104	Mid-infrared optical upconversion by integrating an InAsSb photodetector with a GaAs light emitting diode. , 2007, , .		0
105	Weak antilocalization in a GaAs quantum well in the presence of a strong in-plane magnetic field. AIP Conference Proceedings, 2007, , .	0.3	0
106	Quantum dots for terahertz devices. , 2007, , .		1
107	Strong enhancement of responsivity and tunability of THz quantum-well photodetectors by magnetic field. , 2007, , .		0
108	Frequency quenching of microwave-induced resistance oscillations in a high-mobility two-dimensional electron gas. Physical Review B, 2007, 76, .	1.1	79

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109	Excitonic Fock-Darwin Spectrum Of A Single Quantum Dot. AIP Conference Proceedings, 2007, , .	0.3	0
110	Microwave absorption of a two-dimensional electron gas. AIP Conference Proceedings, 2007, , .	0.3	1
111	Magnetic-field-induced Stoner transition in a quantum Hall ferromagnet at high filling factors. AIP Conference Proceedings, 2007, , .	0.3	0
112	Terahertz quantum-cascade lasers based on a three-well active module. Applied Physics Letters, 2007, 90, 041112.	1.5	151
113	Terahertz Emission in Asymmetric Quantum Wells by Frequency Mixing of Midinfrared Waves. IEEE Journal of Quantum Electronics, 2006, 42, 1157-1174.	1.0	36
114	Photon upconversion devices. , 2006, , .		0
115	<title>THz quantum semiconductor devices</title>. , 2006, 6029, 602901.		0
116	Terahertz quantum well photodetectors. , 2006, , .		1
117	Fock-Darwin spectrum of a single InAs/GaAs quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3748-3751.	0.8	17
118	Device and application of quantum well photodetectors for terahertz region. , 2006, , .		2
119	Dresselhaus spin-orbit coupling in a symmetric (100) GaAs quantum well. Physical Review B, 2006, 74, .	1.1	17
120	Emission from a highly excited single InAs ⁺ GaAs quantum dot in magnetic fields: An excitonic Fock-Darwin diagram. Physical Review B, 2006, 74, .	1.1	40
121	Terahertz quantum cascade lasers: Fabrication, characterization, and doping effect. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 778-782.	0.9	14
122	Observation of resonant tunneling through a self-assembled InAs quantum dot layer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 704-707.	0.9	0
123	Optical upconverter with integrated heterojunction phototransistor and light-emitting diode. Applied Physics Letters, 2006, 88, 073501.	1.5	18
124	Observation of resonant tunneling through a self-assembled InAs quantum dot layer. Applied Physics Letters, 2006, 88, 043103.	1.5	9
125	Wafer-fused mid-infrared optical up-converter based on MOCVD grown InSb. , 2005, , .		2
126	Terahertz quantum well photodetectors. , 2005, , .		0

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127	Individual band mobilities in a double quantum well. AIP Conference Proceedings, 2005, , .	0.3	0
128	Charge Redistribution Spectroscopy as a Probe of Spin Phenomena in Quantum Dots. AIP Conference Proceedings, 2005, , .	0.3	0
129	Pressure tuning of GaInNAs laser diodes in external cavity. , 2005, , .		6
130	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 011114.	1.5	66
131	Quantum Hall ferromagnet at high filling factors: A magnetic-field-induced Stoner transition. Physical Review B, 2005, 72, .	1.1	37
132	AlGaAs emitter-GaAs barrier terahertz detector with a 2.3 THz threshold. Applied Physics Letters, 2005, 86, 071112.	1.5	46
133	Midinfrared optical upconverter. Applied Physics Letters, 2005, 86, 201103.	1.5	26
134	Role of Sb in the growth and optical properties of 1.55- μ m GaInN(Sb)As-GaNAs quantum-well structures by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 181908.	1.5	13
135	Two-band electron transport in a double quantum well. Physical Review B, 2005, 71, .	1.1	30
136	High power blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. Semiconductor Science and Technology, 2005, 20, 809-813.	1.0	36
137	High mobility two-dimensional electron gas in AlGaIn-GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. Applied Physics Letters, 2005, 86, 102106.	1.5	56
138	Background-limited terahertz quantum-well photodetector. Applied Physics Letters, 2005, 86, 231103.	1.5	121
139	Effect of doping concentration on the performance of terahertz quantum-cascade lasers. Applied Physics Letters, 2005, 87, 141102.	1.5	75
140	Thermopower of a double quantum well in a parallel magnetic field. Physical Review B, 2004, 70, .	1.1	6
141	Long time relaxation phenomena of a two-dimensional electron system within integer quantum Hall plateau regimes after magnetic field sweeps. Physical Review B, 2004, 69, .	1.1	30
142	Optical phonons in Al _x Ga _{1-x} As: Raman spectroscopy. Physical Review B, 2004, 70, .	1.1	40
143	Excitonic Energy Shell Structure of Self-Assembled InGaAs/GaAs Quantum Dots. Physical Review Letters, 2004, 92, 187402.	2.9	111
144	Studies of oxide desorption from GaAs substrates via Ga ₂ O ₃ to Ga ₂ O conversion by exposure to Ga flux. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1534.	1.6	51

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145	1.5 μm to 0.87 μm optical upconversion using wafer fusion technology. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 788.	0.9	18
146	FURTHER EVIDENCE FOR A COLLAPSE OF THE EXCHANGE-ENHANCED SPIN SPLITTING IN TWO DIMENSIONAL SYSTEMS. International Journal of Modern Physics B, 2004, 18, 3597-3602.	1.0	2
147	Thermopower and weak localization. Semiconductor Science and Technology, 2004, 19, 1291-1299.	1.0	4
148	Microwave radiation induced magneto-oscillations in the longitudinal and transverse resistance of a two-dimensional electron gas. Solid State Communications, 2004, 129, 341-345.	0.9	89
149	Growth optimisation of the GaN layers and GaN/AlGaIn heterojunctions on bulk GaN substrates using plasma-assisted molecular beam epitaxy. Physica Status Solidi A, 2004, 201, 320-323.	1.7	36
150	Optimized GaAs λ -AlGaAs light-emitting diodes and high efficiency wafer-fused optical up-conversion devices. Journal of Applied Physics, 2004, 96, 5243-5248.	1.1	48
151	Coupled Electron-Phonon Modes in Optically Pumped Resonant Intersubband Lasers. Physical Review Letters, 2003, 90, 077402.	2.9	81
152	Tunnel current in quantum dot infrared photodetectors. Journal of Applied Physics, 2003, 93, 1320-1322.	1.1	46
153	Exciton Dephasing in Quantum Dot Molecules. Physical Review Letters, 2003, 91, 267401.	2.9	100
154	Cutoff tailorability of heterojunction terahertz detectors. Applied Physics Letters, 2003, 82, 139-141.	1.5	39
155	Infrared reflectivity of (GaAs) m /(AlAs) n superlattices. Applied Physics Letters, 2003, 83, 3683-3685.	1.5	13
156	Thermopower of a double quantum well based on GaAs. Physical Review B, 2003, 67, .	1.1	13
157	QWIP-LED PIXELLESS THERMAL IMAGING DEVICE. Selected Topics in Electronics and Systems, 2003, , 299-313.	0.2	2
158	Intersubband transitions in InGaInAs/GaAs quantum wells. Applied Physics Letters, 2002, 81, 1836-1838.	1.5	38
159	QWIPs DESIGNED FOR HIGH ABSORPTION AND HIGH OPERATING TEMPERATURE. International Journal of High Speed Electronics and Systems, 2002, 12, 803-819.	0.3	10
160	QWIP-LED PIXELLESS THERMAL IMAGING DEVICE. International Journal of High Speed Electronics and Systems, 2002, 12, 891-905.	0.3	3
161	Thermal Oxidation of III-V Materials and Heterostructures. Journal of the Electrochemical Society, 2002, 149, C581.	1.3	6
162	Reflection high-energy electron diffraction observation of the dynamics of semiconductor quantum dot formation and decay. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 2210.	1.6	5

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163	High absorption GaAs/AlGaAs quantum well infrared photodetectors. Semiconductor Science and Technology, 2002, 17, L41-L43.	1.0	7
164	Pixelless thermal imaging with integrated quantum-well infrared photodetector and light-emitting diode. IEEE Photonics Technology Letters, 2002, 14, 182-184.	1.3	47
165	Band-gap energy of $\text{In}_x\text{Ga}_{1-x}\text{N}_y\text{As}_{1-y}$ as a function of N content. Physical Review B, 2002, 66, .	1.1	59
166	Resistively Detected Nuclear Magnetic Resonance in the Quantum Hall Regime: Possible Evidence for a Skyrme Crystal. Physical Review Letters, 2002, 88, 256807.	2.9	75
167	InAs/GaAs(100) self-assembled quantum dots: arsenic pressure and capping effects. Journal of Crystal Growth, 2002, 236, 145-154.	0.7	42
168	Inhomogeneous broadening in quantum dots with ternary aluminum alloys. Applied Physics Letters, 2001, 79, 2701-2703.	1.5	22
169	High absorption (>90%) quantum-well infrared photodetectors. Applied Physics Letters, 2001, 79, 4237-4239.	1.5	66
170	Quantum dot infrared photodetectors. Applied Physics Letters, 2001, 78, 79-81.	1.5	293
171	Coupling and Entangling of Quantum States in Quantum Dot Molecules. Science, 2001, 291, 451-453.	6.0	759
172	Intersubband Raman Laser. Applied Physics Letters, 2001, 78, 3580-3582.	1.5	50
173	Optimization of p-doping in GaAs photon-recycling light-emitting diodes operated at low temperature. Semiconductor Science and Technology, 2001, 16, L21-L23.	1.0	9
174	Transient photocurrent overshoot in quantum-well infrared photodetectors. Applied Physics Letters, 2001, 79, 2094-2096.	1.5	17
175	Heterojunction wavelength-tunable far-infrared photodetectors with response out to 70 μm . Applied Physics Letters, 2001, 78, 2241-2243.	1.5	39
176	Coupled InAs/GaAs quantum dots with well-defined electronic shells. Applied Physics Letters, 2000, 76, 2268-2270.	1.5	75
177	Widely tunable self-assembled quantum dot lasers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 578-581.	0.9	13
178	Temperature dependence of photoresponse in p-type $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ multiple quantum wells: Theory and experiment. Physical Review B, 2000, 61, 13798-13804.	1.1	8
179	Quasi-phase matched second-harmonic generation in an $\text{Al}_x\text{Ga}_{1-x}\text{As}$ asymmetric quantum-well waveguide using ion-implantation-enhanced intermixing. Applied Physics Letters, 2000, 77, 4247-4249.	1.5	20
180	Low-frequency impedance of quantized Hall conductors. Physical Review B, 2000, 62, 12990-12996.	1.1	6

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181	Grazing-angle intersubband absorption in n-doped GaAs multiple quantum wells. <i>Physical Review B</i> , 2000, 61, 13050-13054.	1.1	11
182	Addition spectrum of a lateral dot from Coulomb and spin-blockade spectroscopy. <i>Physical Review B</i> , 2000, 61, R16315-R16318.	1.1	369
183	Enhanced degradation resistance of quantum dot lasers to radiation damage. <i>Applied Physics Letters</i> , 2000, 77, 624-626.	1.5	61
184	GaAs/AlGaAs quantum-well photodetector for visible and middle infrared dual-band detection. <i>Applied Physics Letters</i> , 2000, 77, 2437-2439.	1.5	54
185	Asymmetry in the dark current low frequency noise characteristics of B^{C} and B^{C} quantum well infrared photodetectors from 10 to 80 K. <i>Journal of Applied Physics</i> , 2000, 87, 2400-2407.	1.1	6
186	Determination of the size, shape, and composition of indium-flashed self-assembled quantum dots by transmission electron microscopy. <i>Journal of Applied Physics</i> , 2000, 88, 2272-2277.	1.1	49
187	Few-Electron Open Dots: Single Level Transport. <i>Physical Review Letters</i> , 1999, 83, 1838-1841.	2.9	37
188	Pixel-less infrared imaging based on the integration of an n-type quantum-well infrared photodetector with a light-emitting diode. <i>Applied Physics Letters</i> , 1999, 75, 563-565.	1.5	27
189	Intersubband infrared detector with optimized valence band quantum wells for $3\text{--}5\ \mu\text{m}$ wavelength region. <i>Journal of Applied Physics</i> , 1999, 85, 2972-2976.	1.1	22
190	Phase Diagram for the Breakdown of the Quantum Hall Effect. <i>Physical Review Letters</i> , 1999, 82, 1249-1252.	2.9	28
191	Collapse of the Zeeman gap in quantum dots due to electronic correlations. <i>Physical Review B</i> , 1999, 59, 2801-2806.	1.1	54
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193	Manipulating the energy levels of semiconductor quantum dots. <i>Physical Review B</i> , 1999, 59, 15368-15373.	1.1	169
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